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			<ol> <li>Preliminary investigation of hafnium oxide deposited via atomic layer chemical (ALCVD)</li> <li>Conley, J.F., Jr.; Ono, Y.; Tweet, D.J.; Zhuang, W.; Khaiser, M.; Solanki, R.; Integrated Reliability Workshop Final Report, 2001. 2001 IEEE International 15-18 Oct. 2001 Page(s):11 - 15</li> </ol>			
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